N-Channel Super Junction Power MOSFET Ⅳ

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

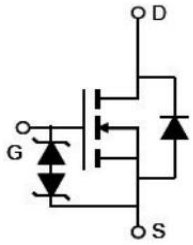
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）

$V_{DS\ min@Tjmax}$	550	V
$R_{DS(ON)TYP.}$	180	mΩ
I_D	13.5	A
Qg	19	nC



Schematic diagram

✧ **Intrinsic fast-recovery body diode**

Package Marking And Ordering Information

Device	Device Package	Marking
NCE50NF220K	TO-252	NCE50NF220K

TO-252

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	500	V
Gate-Source Voltage (V_{DS}=0V) ,AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (V_{DS}=0V) ,DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	13.5	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	9.45	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	40.5	A
Maximum Power Dissipation(Tc=25℃)	P_D	109	W
Derate above 25°C		0.72	W/°C
Single pulse avalanche current **(Note 2)**	I_{AS}	3	A
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15	V/ns
Drain Source voltage slope， V_{DS} ≤480 V	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	1.37	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250uA	500			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=500V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=500V,V_{GS}=0V			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±200	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	3		5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=6.5A		180	220	mΩ
Dynamic Characteristics						
Gate Resistance	Rg	F=1MHZ, D-S short		15		Ω
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1MHz		846		pF
Output Capacitance	C_{oss}			46		pF
Reverse Transfer Capacitance	C_{rss}			1.8		pF
Total Gate Charge	Q_g	V_{DS}=380V,I_D=6.5A, V_{GS}=10V		19		nC
Gate-Source Charge	Q_{gs}			7.3		nC
Gate-Drain Charge	Q_{gd}			5.7		nC
Gate plateau voltage	Vgp			6.6		V
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=6.5A, R_G=4Ω,V_{GS}=10V		8		nS
Turn-on Rise Time	t_r			10		nS
Turn-Off Delay Time	$t_{d(off)}$			41		nS
Turn-Off Fall Time	t_f			10		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			13.5	A
Pulsed-Source-drain current(Body Diode)	I_{SDM}				40.5	A
Forward on voltage	V_{SD}	Tj=25°C,I_{SD}=13.5A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F6.5A, di/dt=100A/μs		150		nS
Reverse Recovery Charge	Q_{rr}			0.34		uC
Peak reverse recovery current	I_{rrm}			4.5		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Output characteristics

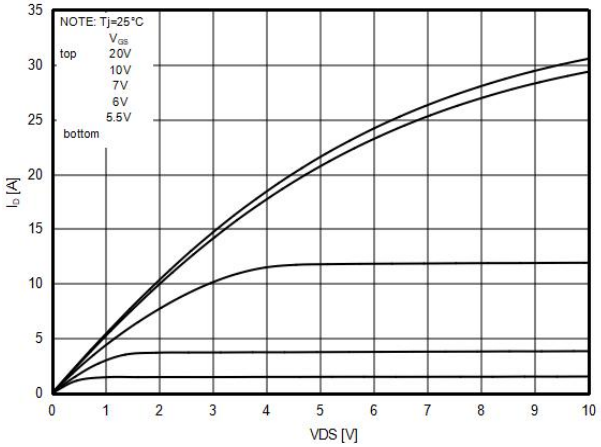


Figure2. Transfer characteristics

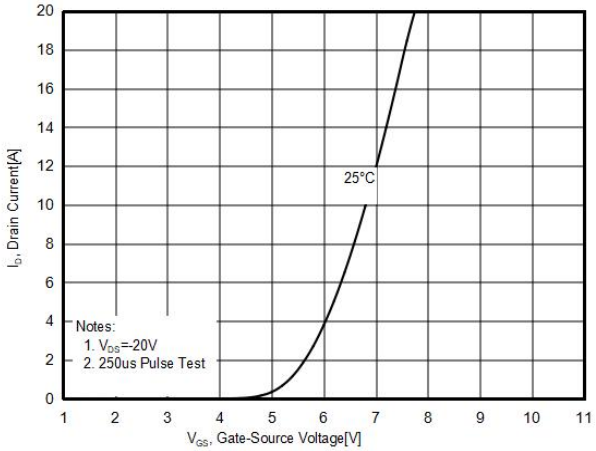


Figure3. $R_{DS(ON)}$ vs Junction Temperature

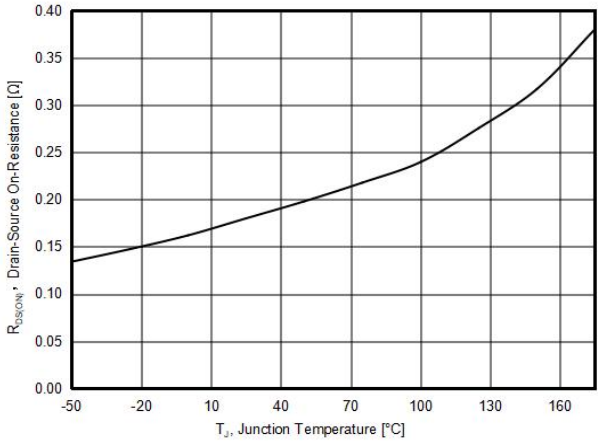


Figure4. BV_{DSS} vs Junction Temperature

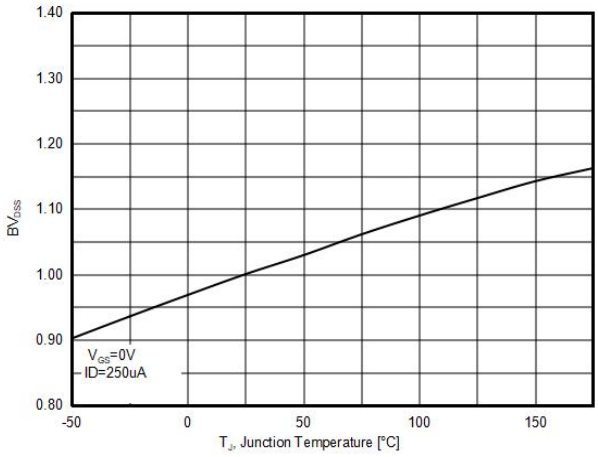


Figure5. Maximum I_D vs Junction Temperature

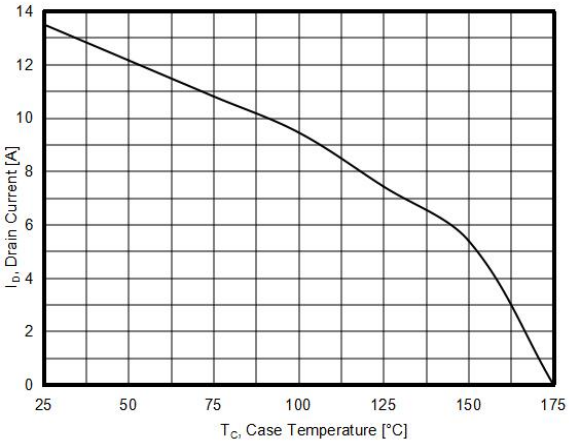


Figure6. Gate charge waveforms

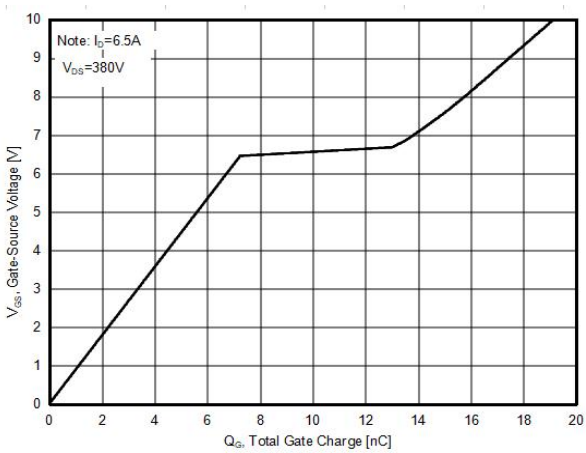


Figure7. Static drain-source on resistance

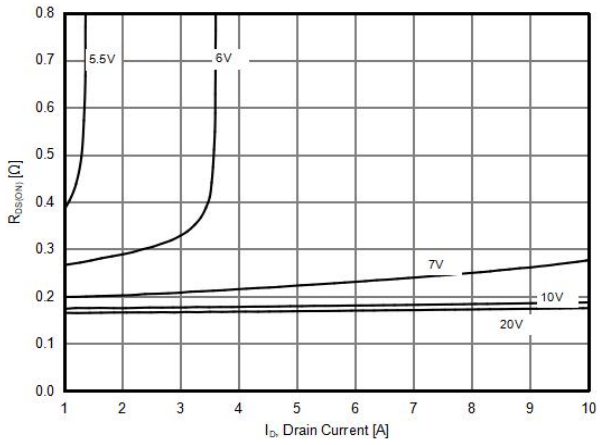


Figure8. Source-Drain Diode Forward Voltage

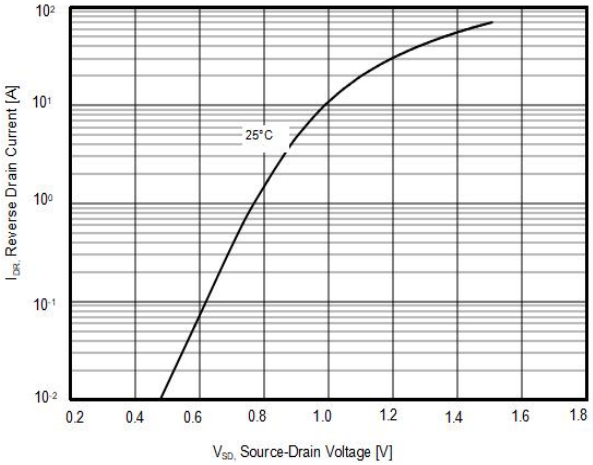


Figure9. Capacitance

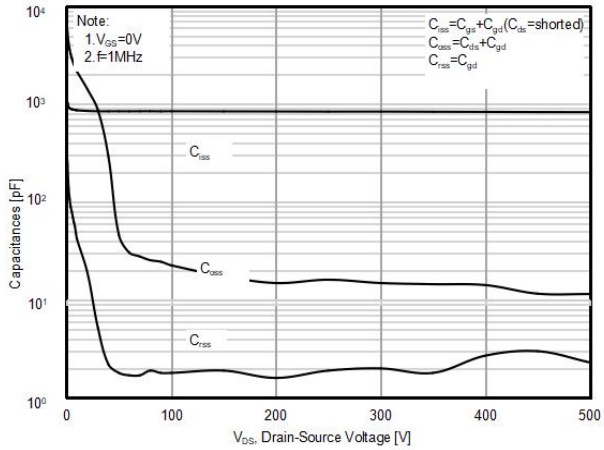
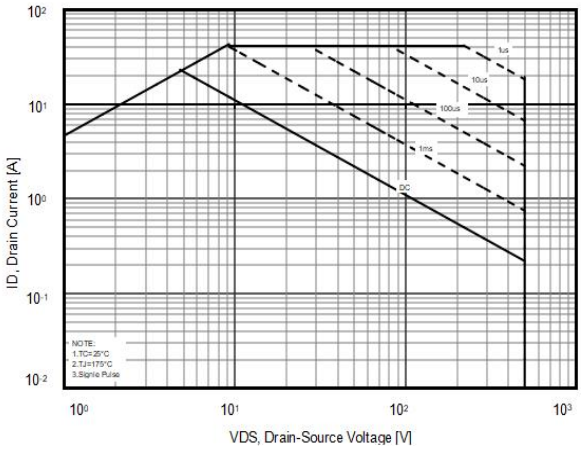
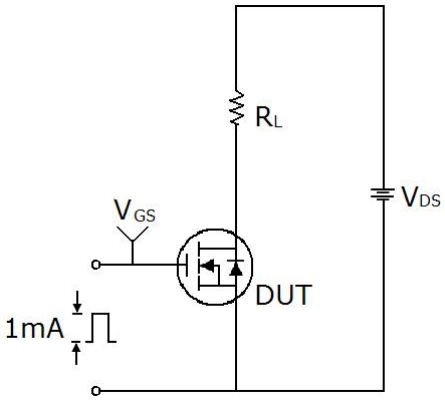


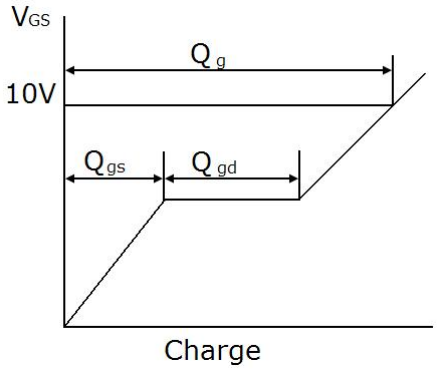
Figure10. Safe operating area



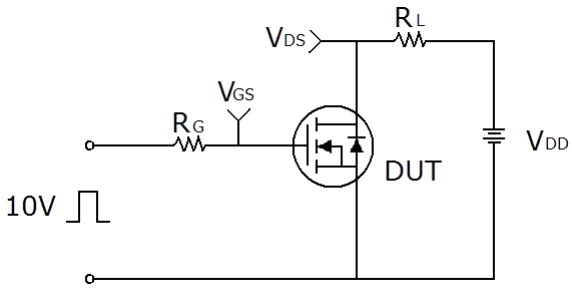
Test circuit

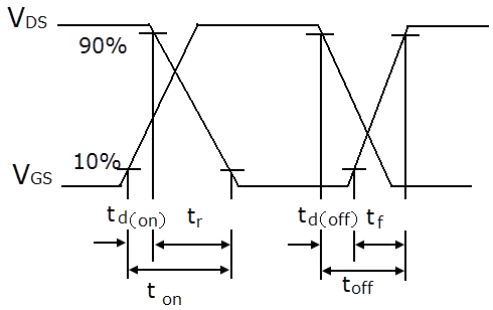
1）Gate charge test circuit & Waveform



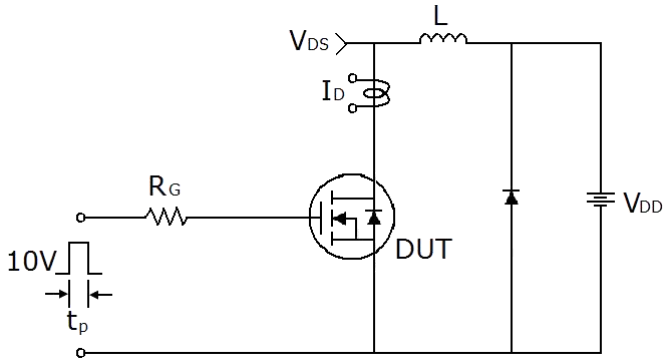


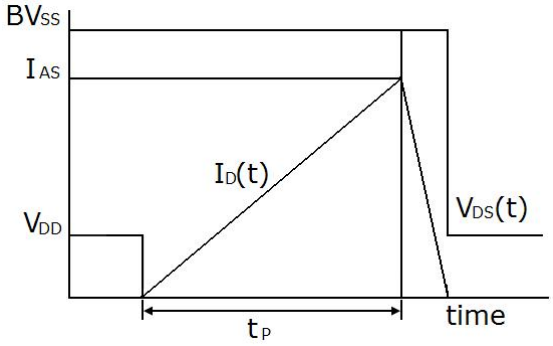
2）Switch Time Test Circuit：



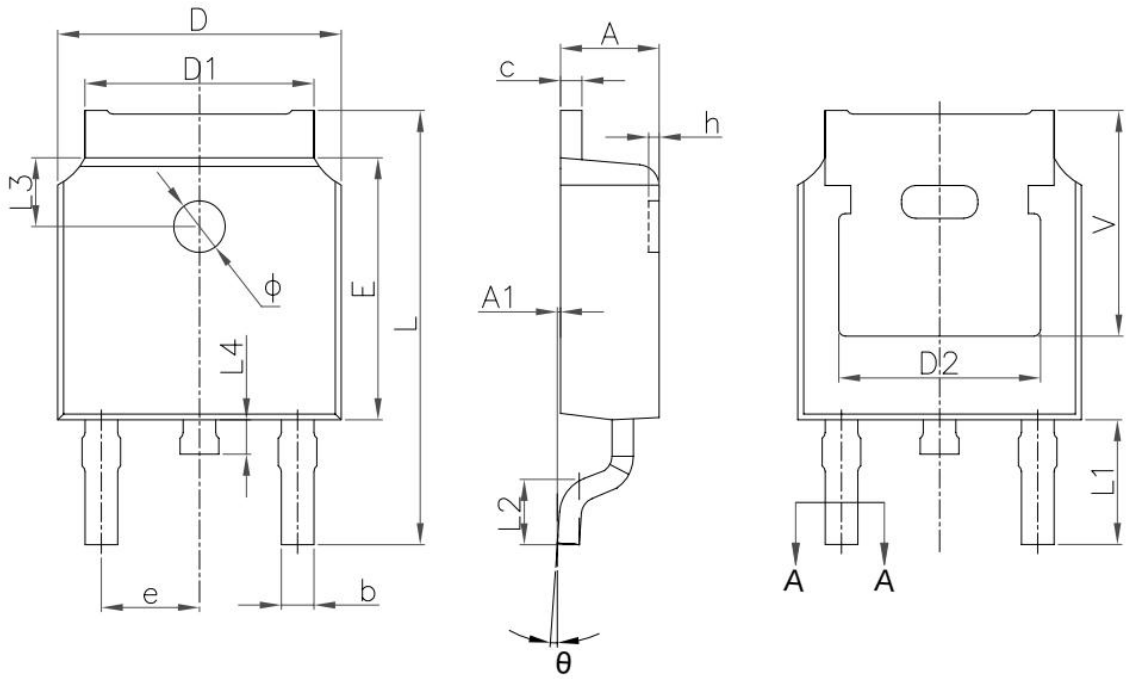


3）Unclamped Inductive Switching Test Circuit & Waveforms





TO-252-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.13	0.000	0.005
b	0.66	0.86	0.026	0.033
b1	0.73	0.79	0.029	0.031
c	0.46	0.58	0.018	0.023
c1	0.50	0.52	0.020	0.020
D	6.50	6.70	0.256	0.264
D1	5.10	5.46	0.201	0.215
D2	4.83 REF		0.19REF	
E	6.00	6.20	0.236	0.244
e	2.19	2.39	0.086	0.094
L	9.80	10.40	0.386	0.409
L1	2.90 REF		0.11REF	
L2	1.40	1.70	0.055	
L3	1.60 REF		0.06REF	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012

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